

TOSHIBA

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

TIM6472-16EL

FEATURES

- ·BROAD BAND INTERNALLY MATCHED FET
- ·HIGH POWER

P1dB= 42.5dBm at 6.4GHz to 7.2GHz

·HIGH GAIN

G1dB= 11.0dB at 6.4GHz to 7.2GHz

·LOW INTERMODULATION DISTORTION

IM3(MIN.)= -40dBc at Pout= 30.5dBm

Single Carrier Level

·HERMETICALLY SEALED PACKAGE



RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 10V IDSset= 2.8A f = 6.4 to 7.2GHz	dBm	41.5	42.5	_
Power Gain at 1dB Gain Compression Point	G1dB		dB	10.0	11.0	_
Drain Current	IDS1		Α	_	4.4	5.0
Gain Flatness	ΔG		dB			±0.8
Power Added Efficiency	ηadd		%	_	37	_
3rd Order Intermodulation Distortion	IM3	Two Tone Test Po= 30.5dBm, Δ f= 5MHz (Single Carrier Level)	dBc	-40	-45	_
Drain Current	IDS2		Α	_	4.4	5.0
Channel Temperature Rise	ΔTch	(VDS X IDS + Pin – P1dB) X Rth(c-c)	°C	_	_	80

Recommended Gate Resistance(Rg): 68 Ω

ELECTRICAL CHARACTERISTICS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 5.2A	S	_	5.2	_
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 40mA	V	-1.0	-1.9	-4.0
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	А	_	8.8	14.0
Gate-Source Breakdown Voltage	VGSO	IGS= -180 _μ A	V	-5.0	-7.0	
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	_	1.5	1.8

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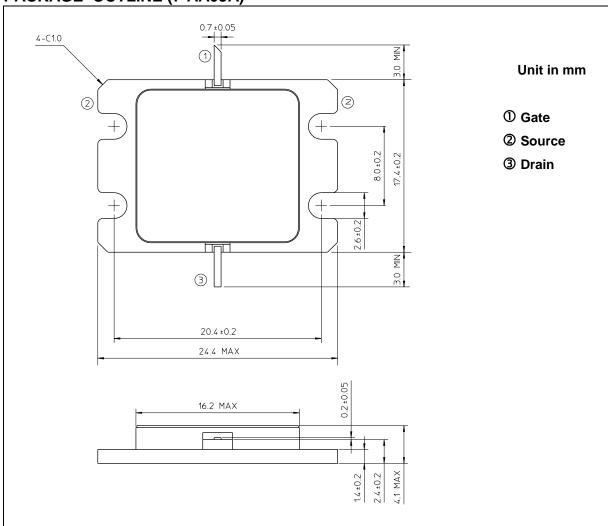


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ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	А	14.0
Total Power Dissipation (Tc= 25°C)	PT	W	83.3
Channel Temperature	Tch	°C	175
Storage	Tstg	°C	-65 to +175

PACKAGE OUTLINE (7-AA05A)



ANDLING PRECAUTIONS FOR PACKAGE MODEL

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.



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MICROWAVE POWER GAAS FET TIM6472-16EL

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